D OR DGN PACKAGE

(TOP VIEW)

2

3

SHUTDOWNE

BYPASS□

IN+□

SLOS312A - JUNE 2000 - REVISED JUNE 2000

 $\square$   $\vee_{\bigcirc}$ 

 ☐ GND

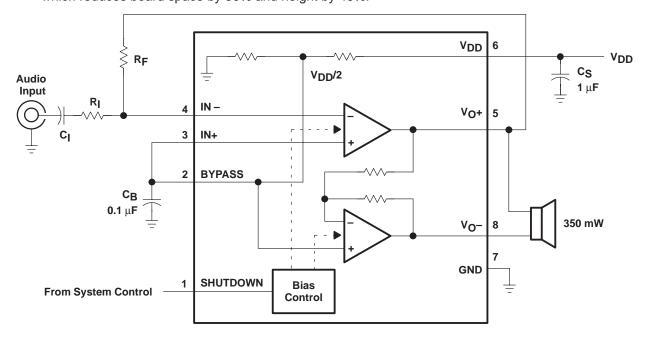
 $\square$   $\vee_{DD}$ 

□ V<sub>O</sub>+

- Fully Specified for 3.3-V and 5-V Operation
- Wide Power Supply Compatibility 2.5 V - 5.5 V
- Output Power for  $R_1 = 8 \Omega$ 
  - 350 mW at  $V_{DD} = 5 V$
  - 250 mW at  $V_{DD} = 3.3 V$
- **Ultralow Supply Current in Shutdown Mode . . . 0.15** μ**A**
- **Thermal and Short-Circuit Protection**
- **Surface-Mount Packaging** 
  - SOIC
  - PowerPAD™ MSOP

## description

The TPA321 is a bridge-tied load (BTL) audio power amplifier developed especially for low-voltage applications where internal speakers are required. Operating with a 3.3-V supply, the TPA321 can deliver 250-mW of continuous power into a BTL 8-Ω load at less than 1% THD+N throughout voice band frequencies. Although this device is characterized out to 20 kHz, its operation was optimized for narrower band applications such as cellular communications. The BTL configuration eliminates the need for external coupling capacitors on the output in most applications, which is particularly important for small battery-powered equipment. This device features a shutdown mode for power-sensitive applications with a guiescent current of 0.15 µA during shutdown. The TPA321 is available in an 8-pin SOIC surface-mount package and the surface-mount PowerPAD™ MSOP, which reduces board space by 50% and height by 40%.





Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

PowerPAD is a trademark of Texas Instruments.



#### **AVAILABLE OPTIONS**

|               | PACKAGEI                          | MSOP           |               |
|---------------|-----------------------------------|----------------|---------------|
| TA            | SMALL OUTLINE <sup>†</sup><br>(D) | MSOP†<br>(DGN) | SYMBOLIZATION |
| -40°C to 85°C | TPA321D                           | TPA321DGN      | AJB           |

<sup>†</sup> The D and DGN packages are available taped and reeled. To order a taped and reeled part, add the suffix R to the part number (e.g., TPA321DR).

#### **Terminal Functions**

| TERMINA          | \L  | 1/0 | DESCRIPTION  |
|------------------|-----|-----|--|
| NAME             | NO. | "0  | DESCRIPTION  |
| BYPASS           | 2   | ı   | BYPASS is the tap to the voltage divider for internal mid-supply bias. This terminal should be connected to a $0.1$ - $\mu$ F capacitor when used as an audio amplifier. |
| GND              | 7   |     | GND is the ground connection.  |
| IN-              | 4   | ı   | IN – is the inverting input. IN – is typically used as the audio input terminal.   |
| IN+              | 3   | I   | IN+ is the noninverting input. IN+ is typically tied to the BYPASS terminal for SE operations.   |
| SHUTDOWN         | 1   | ı   | SHUTDOWN places the entire device in shutdown mode when held high (IDD < 1 $\mu$ A).   |
| $V_{DD}$         | 6   |     | V <sub>DD</sub> is the supply voltage terminal.  |
| V <sub>O</sub> + | 5   | 0   | V <sub>O</sub> + is the positive BTL output.   |
| VO-              | 8   | 0   | V <sub>O</sub> – is the negative BTL output.   |

## absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

| Supply voltage, V <sub>DD</sub>                            | 6 V   |
|--|---|
| Input voltage, V <sub>I</sub>                              |   |
| Continuous total power dissipation                         | internally limited (see Dissipation Rating Table) |
| Operating free-air temperature range, T <sub>A</sub>       | –40°C to 85°C                                     |
| Operating junction temperature range, T <sub>J</sub>       | –40°C to 150°C                                    |
| Storage temperature range, T <sub>stg</sub>                |   |
| Lead temperature 1,6 mm (1/16 inch) from case for 10 secon | nds 260°C   |

<sup>‡</sup> Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

#### **DISSIPATION RATING TABLE**

| PACKAGE | $T_{\hbox{\scriptsize A}} \leq 25^{\circ}\hbox{\scriptsize C}$ | DERATING FACTOR | T <sub>A</sub> = 70°C | T <sub>A</sub> = 85°C |
|---------|--|-----------------|-----------------------|-----------------------|
| D       | 725 mW   | 5.8 mW/°C       | 464 mW                | 377 mW                |
| DGN     | 2.14 W§  | 17.1 mW/°C      | 1.37 W                | 1.11 W                |

<sup>§</sup> Please see the Texas Instruments document, PowerPAD Thermally Enhanced Package Application Report (literature number SLMA002), for more information on the PowerPAD<sup>TM</sup> package. The thermal data was measured on a PCB layout based on the information in the section entitled Texas Instruments Recommended Board for PowerPAD on page 33 of the before mentioned document.

## recommended operating conditions

|  | MIN | MAX | UNIT |
|--|-----|-----|------|
| Supply voltage, V <sub>DD</sub>                | 2.5 | 5.5 | V    |
| Operating free-air temperature, T <sub>A</sub> | -40 | 85  | °C   |



# electrical characteristics at specified free-air temperature, $V_{DD}$ = 3.3 V, $T_A$ = 25°C (unless otherwise noted)

|                     | PARAMETER                                       | TEST CONDITIONS                            | MIN | TYP  | MAX | UNIT |
|---------------------|---|--|-----|------|-----|------|
| IVosl               | Output offset voltage (measured differentially) |  |     | 5    | 20  | mV   |
| PSRR                | Power supply rejection ratio                    | $V_{DD} = 3.2 \text{ V to } 3.4 \text{ V}$ |     | 85   |     | dB   |
| $I_{DD}$            | Supply current (see Figure 3)                   |  |     | 0.7  | 1.5 | mA   |
| I <sub>DD(SD)</sub> | Supply current, shutdown mode (see Figure 4)    |  |     | 0.15 | 5   | μΑ   |

## operating characteristics, V<sub>DD</sub> = 3.3 V, T<sub>A</sub> = 25°C, R<sub>L</sub> = 8 $\Omega$

|                | PARAMETER                            |  | TEST CONDITIONS                           |  | TYP  | MAX | UNIT    |
|----------------|--------------------------------------|--|---|--|------|-----|---------|
| PO             | Output power, see Note 1             | THD = 0.5%,                                | See Figure 9                              |  | 250  |     | mW      |
| THD + N        | Total harmonic distortion plus noise | $P_0 = 250 \text{ mW},$<br>Gain = 2,       | f = 20 Hz to 4 kHz,<br>See Figure 7       |  | 1.3% |     |         |
|                | Maximum output power bandwidth       | $A_V = -2 \text{ V/V},$<br>See Figure 7    | THD = 3%,                                 |  | 10   |     | kHz     |
| B <sub>1</sub> | Unity-gain bandwidth                 | Open Loop,                                 | See Figure 15                             |  | 1.4  |     | MHz     |
|                | Supply ripple rejection ratio        | f = 1 kHz,<br>See Figure 2                 | $C_B = 1 \mu F$ ,                         |  | 71   |     | dB      |
| Vn             | Noise output voltage                 | $A_V = -1 \text{ V/V},$ $R_L = 32 \Omega,$ | C <sub>B</sub> = 0.1 μF,<br>See Figure 19 |  | 15   | ·   | μV(rms) |

NOTE 1: Output power is measured at the output terminals of the device at f = 1 kHz.

# electrical characteristics at specified free-air temperature, $V_{DD}$ = 5 V, $T_A$ = 25°C (unless otherwise noted)

|                     | PARAMETER                                       | TEST CONDITIONS                            | MIN | TYP  | MAX | UNIT |
|---------------------|---|--|-----|------|-----|------|
| IVosl               | Output offset voltage (measured differentially) |  | ·   | 5    | 20  | mV   |
| PSRR                | Power supply rejection ratio                    | $V_{DD} = 4.9 \text{ V to } 5.1 \text{ V}$ |     | 78   |     | dB   |
| I <sub>DD</sub>     | Supply current (see Figure 3)                   |  |     | 0.7  | 1.5 | mA   |
| I <sub>DD(SD)</sub> | Supply current, shutdown mode (see Figure 4)    |  |     | 0.15 | 5   | μΑ   |

# operating characteristics, V<sub>DD</sub> = 5 V, T<sub>A</sub> = 25°C, R<sub>L</sub> = 8 $\Omega$

|                | PARAMETER                            |  | TEST CONDITIONS                           |  | TYP | MAX | UNIT    |
|----------------|--------------------------------------|--|---|--|-----|-----|---------|
| PO             | Output power                         | THD = 0.5%,                                    | See Figure 13                             |  | 700 |     | mW      |
| THD + N        | Total harmonic distortion plus noise | P <sub>O</sub> = 250 mW,<br>Gain = 2,          | f = 20 Hz to 4 kHz,<br>See Figure 11      |  | 1%  |     |         |
|                | Maximum output power bandwidth       | $A_V = -2 \text{ V/V},$<br>See Figure 11       | THD = 2%,                                 |  | 10  |     | kHz     |
| B <sub>1</sub> | Unity-gain bandwidth                 | Open Loop,                                     | See Figure 16                             |  | 1.4 |     | MHz     |
|                | Supply ripple rejection ratio        | f = 1 kHz,<br>See Figure 2                     | $C_B = 1 \mu F$ ,                         |  | 65  |     | dB      |
| Vn             | Noise output voltage                 | $A_{V} = -1 \text{ V/V},$ $R_{L} = 32 \Omega,$ | C <sub>B</sub> = 0.1 μF,<br>See Figure 20 |  | 15  |     | μV(rms) |

### PARAMETER MEASUREMENT INFORMATION

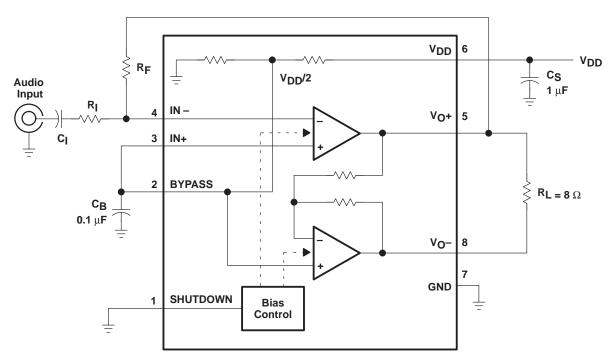


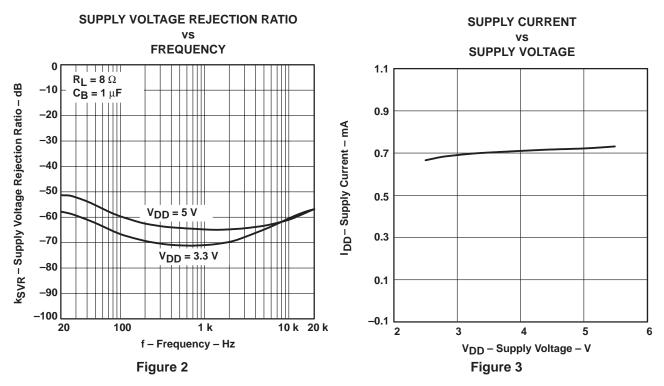
Figure 1. Test Circuit

## **TYPICAL CHARACTERISTICS**

## **Table of Graphs**

|                 |                                      |                    | FIGURE        |
|-----------------|--------------------------------------|--------------------|---------------|
| ksvr            | Supply voltage rejection ratio       | vs Frequency       | 2             |
| I <sub>DD</sub> | Supply current                       | vs Supply voltage  | 3, 4          |
| Do.             | Output power                         | vs Supply voltage  | 5             |
| Po              | Output power                         | vs Load resistance | 6             |
| THD+N           | Total harmonic distortion plus noise | vs Frequency       | 7, 8, 11, 12  |
| IIID+N          | Total Harmonic distortion plus hoise | vs Output power    | 9, 10, 13, 14 |
|                 | Open loop gain and phase             | vs Frequency       | 15, 16        |
|                 | Closed loop gain and phase           | vs Frequency       | 17, 18        |
| Vn              | Output noise voltage                 | vs Frequency       | 19, 20        |
| $P_{D}$         | Power dissipation                    | vs Output power    | 21, 22        |





# SUPPLY CURRENT (SHUTDOWN) vs

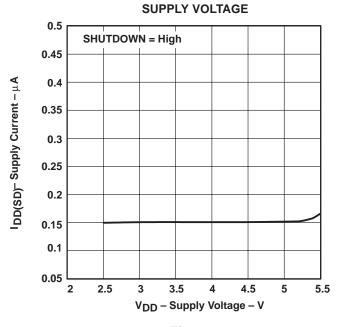


Figure 4

# **OUTPUT POWER SUPPLY VOLTAGE** 1000 **THD+N 1%** 800 Po - Output Power - mW 600 $R_L = 8 \Omega$ 400 $R_L = 32 \Omega$ 200 0 2 2.5 3.5 4.5 5.5 V<sub>DD</sub> – Supply Voltage – V

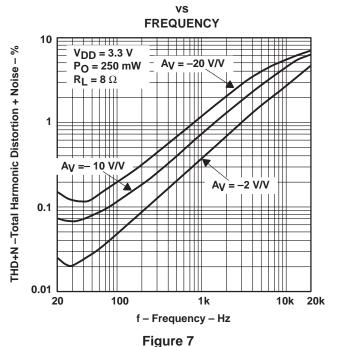
Figure 5

## **OUTPUT POWER LOAD RESISTANCE** 800 THD+N = 1% 700 600 Po - Output Power - mW $V_{DD} = 5 V$ 500 400 300 $V_{DD} = 3.3 V$ 200 100 0 64 8 16 32 40 56 $R_L$ – Load Resistance – $\Omega$

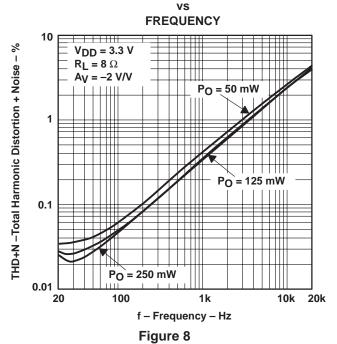


Figure 6

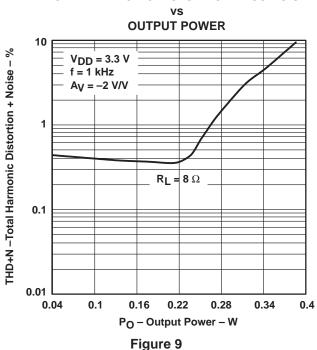
## TOTAL HARMONIC DISTORTION PLUS NOISE



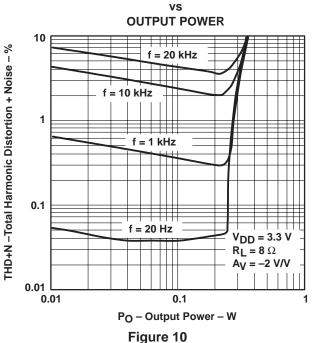
#### TOTAL HARMONIC DISTORTION PLUS NOISE



## TOTAL HARMONIC DISTORTION PLUS NOISE

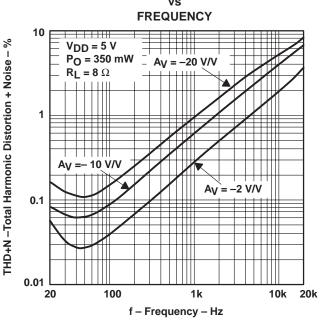


## TOTAL HARMONIC DISTORTION PLUS NOISE



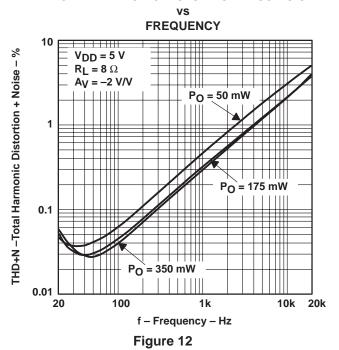


## TOTAL HARMONIC DISTORTION PLUS NOISE

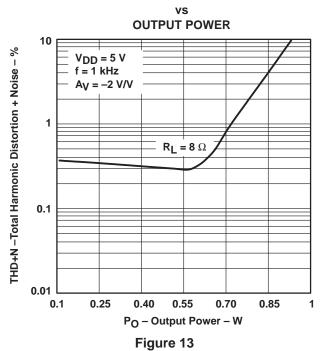


#### Figure 11

#### TOTAL HARMONIC DISTORTION PLUS NOISE



#### TOTAL HARMONIC DISTORTION PLUS NOISE



#### TOTAL HARMONIC DISTORTION PLUS NOISE

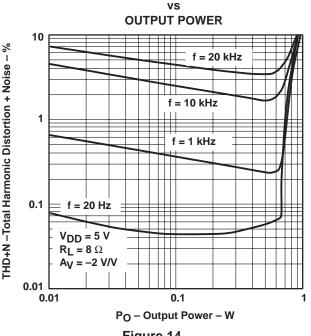


Figure 14



# OPEN-LOOP GAIN AND PHASE

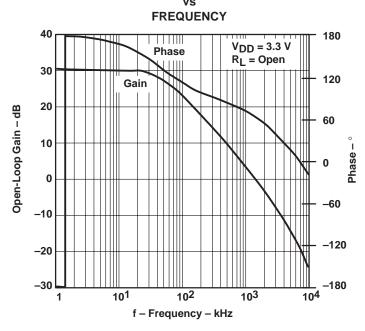


Figure 15

## **OPEN-LOOP GAIN AND PHASE**

vs **FREQUENCY** 40 180  $V_{DD} = 5 V$ Phase R<sub>L</sub> = Open 30 120 Gain 20 Open-Loop Gain – dB 60 10 0 -60 -10 -120 -20 -30 -180 10<sup>2</sup> 10<sup>3</sup> 10<sup>4</sup> 101 f - Frequency - kHz

Figure 16



#### **CLOSED-LOOP GAIN AND PHASE**

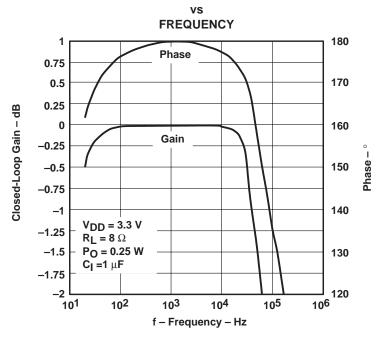


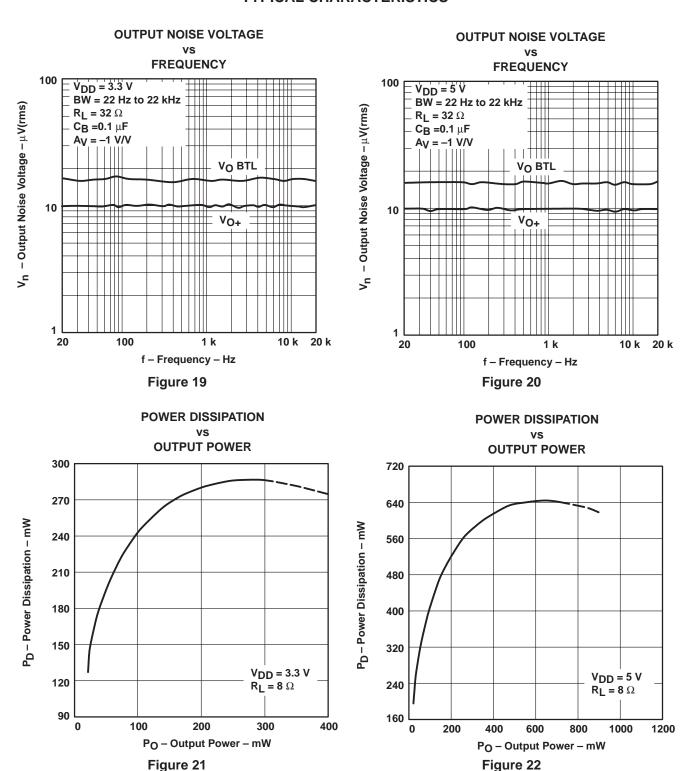
Figure 17

#### **CLOSED-LOOP GAIN AND PHASE**

vs **FREQUENCY** 180 1 Phase 0.75 170 0.5 0.25 Closed-Loop Gain - dB 0 160 Gain -0.25-0.5 150 -0.75 -1 140  $V_{DD} = 5 V$ -1.25  $R_L = 8 \Omega$  $P_0 = 0.35 \text{ W}$ -1.5 130  $C_I = 1 \mu F$ -1.75 -2 120 101 104 105 102 106 f – Frequency – Hz

Figure 18





#### bridge-tied load

Figure 23 shows a linear audio power amplifier (APA) in a BTL configuration. The TPA321 BTL amplifier consists of two linear amplifiers driving both ends of the load. There are several potential benefits to this differential drive configuration but power to the load should be initially considered. The differential drive to the speaker means that as one side is slewing up, the other side is slewing down, and vice versa. This in effect doubles the voltage swing on the load as compared to a ground referenced load. Plugging  $2 \times V_{O(PP)}$  into the power equation, where voltage is squared, yields  $4 \times$  the output power from the same supply rail and load impedance (see equation 1).

$$V_{(rms)} = \frac{V_{O(PP)}}{2\sqrt{2}}$$

$$Power = \frac{V_{(rms)}^{2}}{R_{L}}$$
(1)

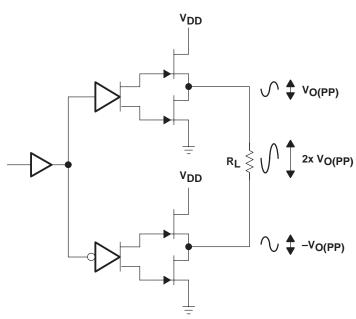


Figure 23. Bridge-Tied Load Configuration

In a typical portable handheld equipment sound channel operating at 3.3 V, bridging raises the power into an  $8-\Omega$  speaker from a single-ended (SE, ground reference) limit of 62.5 mW to 250 mW. In sound power that is a 6-dB improvement, which is loudness that can be heard. In addition to increased power, there are frequency response concerns. Consider the single-supply SE configuration shown in Figure 24. A coupling capacitor is required to block the dc offset voltage from reaching the load. These capacitors can be quite large (approximately 33 μF to 1000 μF) so they tend to be expensive, heavy, occupy valuable PCB area, and have the additional drawback of limiting low-frequency performance of the system. This frequency limiting effect is due to the high pass filter network created with the speaker impedance and the coupling capacitance and is calculated with equation 2.



#### **APPLICATION INFORMATION**

## bridge-tied load versus single-ended mode (continued)

$$f_c = \frac{1}{2\pi R_I C_C} \tag{2}$$

For example, a  $68-\mu F$  capacitor with an  $8-\Omega$  speaker would attenuate low frequencies below 293 Hz. The BTL configuration cancels the dc offsets, eliminating the need for the blocking capacitors. Low-frequency performance is then limited only by the input network and speaker response. Cost and PCB space are also minimized by eliminating the bulky coupling capacitor.

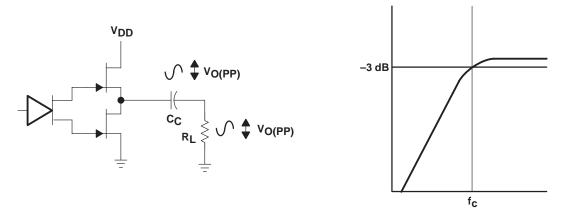


Figure 24. Single-Ended Configuration and Frequency Response

Increasing power to the load does carry a penalty of increased internal power dissipation. The increased dissipation is understandable considering that the BTL configuration produces 4× the output power of a SE configuration. Internal dissipation versus output power is discussed further in the *thermal considerations* section.

### BTL amplifier efficiency

Linear amplifiers are notoriously inefficient. The primary cause of these inefficiencies is voltage drop across the output stage transistors. There are two components of the internal voltage drop. One is the headroom or dc voltage drop that varies inversely to output power. The second component is due to the sinewave nature of the output. The total voltage drop can be calculated by subtracting the RMS value of the output voltage from  $V_{DD}$ . The internal voltage drop multiplied by the RMS value of the supply current,  $I_{DD}$ rms, determines the internal power dissipation of the amplifier.

An easy-to-use equation to calculate efficiency starts out as being equal to the ratio of power from the power supply to the power delivered to the load. To accurately calculate the RMS values of power in the load and in the amplifier, the current and voltage waveform shapes must first be understood (see Figure 25).

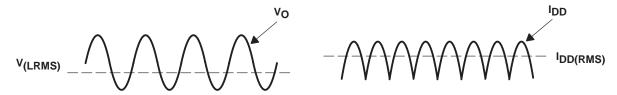


Figure 25. Voltage and Current Waveforms for BTL Amplifiers



## BTL amplifier efficiency (continued)

Although the voltages and currents for SE and BTL are sinusoidal in the load, currents from the supply are very different between SE and BTL configurations. In an SE application the current waveform is a half-wave rectified shape whereas in BTL it is a full-wave rectified waveform. This means RMS conversion factors are different. Keep in mind that for most of the waveform both the push and pull transistors are not on at the same time, which supports the fact that each amplifier in the BTL device only draws current from the supply for half the waveform. The following equations are the basis for calculating amplifier efficiency.

Efficiency = 
$$\frac{P_L}{P_{SUP}}$$
 (3)

Where:

$$P_{L} = \frac{V_{L} \text{rms}^{2}}{R_{L}} = \frac{V_{p}^{2}}{2R_{L}}$$

$$V_{L} \text{rms} = \frac{V_{p}}{\sqrt{2}}$$

$$V_{DD} = \frac{V_{DD}}{2}$$

$$\begin{split} & P_{SUP} \ = \ V_{DD} \ I_{DD} rms \ = \frac{V_{DD} \ 2V_{P}}{\pi \ R_{L}} \\ & I_{DD} rms \ = \frac{2V_{P}}{\pi \ R_{L}} \end{split}$$

Efficiency of a BTL Configuration = 
$$\frac{\pi V_P}{2V_{DD}} = \frac{\pi \left(\frac{P_L R_L}{2}\right)^{1/2}}{2V_{DD}}$$
 (4)

Table 1 employs equation 4 to calculate efficiencies for three different output power levels. The efficiency of the amplifier is quite low for lower power levels and rises sharply as power to the load is increased resulting in a nearly flat internal power dissipation over the normal operating range. The internal dissipation at full output power is less than in the half power range. Calculating the efficiency for a specific system is the key to proper power supply design.

Table 1. Efficiency vs Output Power in 3.3-V 8- $\Omega$  BTL Systems

| OUTPUT POWER (W) | EFFICIENCY<br>(%) | PEAK-to-PEAK<br>VOLTAGE<br>(V) | INTERNAL<br>DISSIPATION<br>(W) |
|------------------|-------------------|--------------------------------|--------------------------------|
| 0.125            | 33.6              | 1.41                           | 0.26                           |
| 0.25             | 47.6              | 2.00                           | 0.29                           |
| 0.375            | 58.3              | 2.45†                          | 0.28                           |

<sup>†</sup> High-peak voltage values cause the THD to increase.

A final point to remember about linear amplifiers (either SE or BTL) is how to manipulate the terms in the efficiency equation to utmost advantage when possible. Note that in equation 4,  $V_{DD}$  is in the denominator. This indicates that as  $V_{DD}$  goes down, efficiency goes up.



## application schematics

Figure 26 is a schematic diagram of a typical handheld audio application circuit, configured for a gain of -10 V/V.

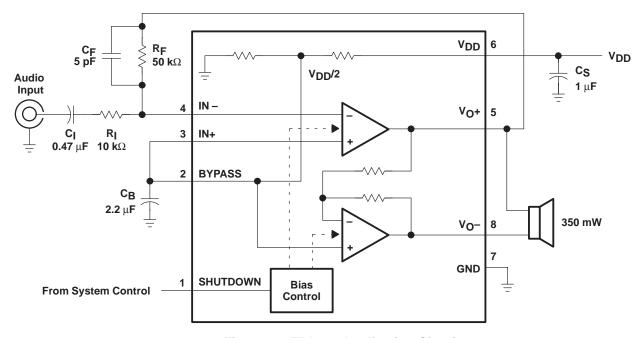


Figure 26. TPA321 Application Circuit

Figure 27 is a schematic diagram of a typical handheld audio application circuit, configured for a gain of -10 V/V with a differential input.

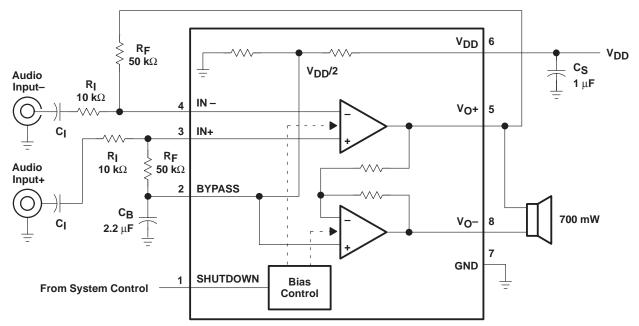


Figure 27. TPA321 Application Circuit With Differential Input



## application schematics (continued)

It is important to note that using the additional  $R_F$  resistor connected between IN+ and BYPASS will cause  $V_{DD}/2$  to shift slightly, which could influence the THD+N performance of the amplifier. Although an additional external op-amp could be used to buffer BYPASS from  $R_F$ , tests in the lab have shown that the THD+N performance is only minimally affected by operating in the fully differential mode as shown in Figure 27. The following sections discuss the selection of the components used in Figures 26 and 27.

### component selection

#### gain setting resistors, RF and RI

The gain for each audio input of the TPA321 is set by resistors  $R_F$  and  $R_I$  according to equation 5 for BTL mode.

BTL Gain = 
$$A_V = -2\left(\frac{R_F}{R_I}\right)$$
 (5)

BTL mode operation brings about the factor 2 in the gain equation due to the inverting amplifier mirroring the voltage swing across the load. Given that the TPA321 is a MOS amplifier, the input impedance is very high, consequently input leakage currents are not generally a concern although noise in the circuit increases as the value of  $R_F$  increases. In addition, a certain range of  $R_F$  values are required for proper start-up operation of the amplifier. Taken together it is recommended that the effective impedance seen by the inverting node of the amplifier be set between 5 k $\Omega$  and 20 k $\Omega$ . The effective impedance is calculated in equation 6.

Effective Impedance = 
$$\frac{R_F R_I}{R_F + R_I}$$
 (6)

As an example, consider an input resistance of 10 k $\Omega$  and a feedback resistor of 50 k $\Omega$ . The BTL gain of the amplifier would be –10 V/V, and the effective impedance at the inverting terminal would be 8.3 k $\Omega$ , which is well within the recommended range.

For high performance applications metal film resistors are recommended because they tend to have lower noise levels than carbon resistors. For values of  $R_F$  above 50  $k\Omega$ , the amplifier tends to become unstable due to a pole formed from  $R_F$  and the inherent input capacitance of the MOS input structure. For this reason, a small compensation capacitor,  $C_F$ , of approximately 5 pF should be placed in parallel with  $R_F$  when  $R_F$  is greater than 50  $k\Omega$ . This, in effect, creates a low-pass filter network with the cutoff frequency defined in equation 7.

$$f_{C} = \frac{1}{2\pi R_{F}C_{F}} \tag{7}$$

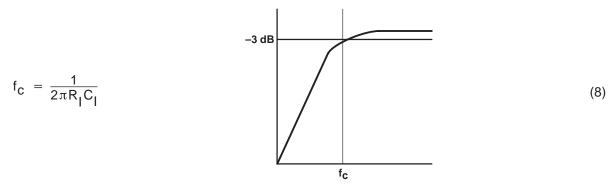
For example, if  $R_F$  is 100 k $\Omega$  and  $C_F$  is 5 pF then  $f_c$  is 318 kHz, which is well outside of the audio range.



#### APPLICATION INFORMATION

## input capacitor, CI

In the typical application an input capacitor,  $C_I$ , is required to allow the amplifier to bias the input signal to the proper dc level for optimum operation. In this case,  $C_I$  and  $R_I$  form a high-pass filter with the corner frequency determined in equation 8.



The value of  $C_I$  is important to consider as it directly affects the bass (low frequency) performance of the circuit. Consider the example where  $R_I$  is 10 k $\Omega$  and the specification calls for a flat bass response down to 40 Hz. Equation 8 is reconfigured as equation 9.

$$C_{\parallel} = \frac{1}{2\pi R_{\parallel} f_{C}} \tag{9}$$

In this example,  $C_I$  is 0.40  $\mu$ F, so one would likely choose a value in the range of 0.47  $\mu$ F to 1  $\mu$ F. A further consideration for this capacitor is the leakage path from the input source through the input network ( $R_I$ ,  $C_I$ ) and the feedback resistor ( $R_F$ ) to the load. This leakage current creates a dc offset voltage at the input to the amplifier that reduces useful headroom, especially in high gain applications. For this reason a low-leakage tantalum or ceramic capacitor is the best choice. When polarized capacitors are used, the positive side of the capacitor should face the amplifier input in most applications, as the dc level there is held at  $V_{DD}/2$ , which is likely higher than the source dc level. It is important to confirm the capacitor polarity in the application.

#### power supply decoupling, CS

The TPA321 is a high-performance CMOS audio amplifier that requires adequate power supply decoupling to ensure the output total harmonic distortion (THD) is as low as possible. Power supply decoupling also prevents oscillations for long lead lengths between the amplifier and the speaker. The optimum decoupling is achieved by using two capacitors of different types that target different types of noise on the power supply leads. For higher frequency transients, spikes, or digital hash on the line, a good low equivalent-series-resistance (ESR) ceramic capacitor, typically 0.1  $\mu$ F, placed as close as possible to the device  $V_{DD}$  lead, works best. For filtering lower-frequency noise signals, a larger aluminum electrolytic capacitor of 10  $\mu$ F or greater placed near the audio power amplifier is recommended.

#### **APPLICATION INFORMATION**

#### midrail bypass capacitor, CB

The midrail bypass capacitor,  $C_B$ , is the most critical capacitor and serves several important functions. During start-up or recovery from shutdown mode,  $C_B$  determines the rate at which the amplifier starts up. The second function is to reduce noise produced by the power supply caused by coupling into the output drive signal. This noise is from the midrail generation circuit internal to the amplifier, which appears as degraded PSRR and THD + N. The capacitor is fed from a 250-k $\Omega$  source inside the amplifier. To keep the start-up pop as low as possible, the relationship shown in equation 10 should be maintained, which insures the input capacitor is fully charged before the bypass capacitor is fully charged and the amplifier starts up.

$$\frac{10}{\left(C_{\mathsf{B}} \times 250 \text{ k}\Omega\right)} \le \frac{1}{\left(R_{\mathsf{F}} + R_{\mathsf{I}}\right) C_{\mathsf{I}}} \tag{10}$$

As an example, consider a circuit where  $C_B$  is 2.2  $\mu$ F,  $C_I$  is 0.47  $\mu$ F,  $R_F$  is 50  $k\Omega$  and  $R_I$  is 10  $k\Omega$ . Inserting these values into the equation 10 we get:

$$18.2 \le 35.5$$

which satisfies the rule. Bypass capacitor,  $C_B$ , values of 2.2  $\mu F$  to 1  $\mu F$  ceramic or tantalum low-ESR capacitors are recommended for the best THD and noise performance.

### using low-ESR capacitors

Low-ESR capacitors are recommended throughout this application. A real (as opposed to ideal) capacitor can be modeled simply as a resistor in series with an ideal capacitor. The voltage drop across this resistor minimizes the beneficial effects of the capacitor in the circuit. The lower the equivalent value of this resistance, the more the real capacitor behaves like an ideal capacitor.

## 5-V versus 3.3-V operation

The TPA321 operates over a supply range of 2.5 V to 5.5 V. This data sheet provides full specifications for 5-V and 3.3-V operation, as these are considered to be the two most common standard voltages. There are no special considerations for 3.3-V versus 5-V operation with respect to supply bypassing, gain setting, or stability. The most important consideration is that of output power. Each amplifier in TPA321 can produce a maximum voltage swing of  $V_{DD} - 1$  V. This means, for 3.3-V operation, clipping starts to occur when  $V_{O(PP)} = 2.3$  V as opposed to  $V_{O(PP)} = 4$  V at 5 V. The reduced voltage swing subsequently reduces maximum output power into an 8- $\Omega$  load before distortion becomes significant.

Operation from 3.3-V supplies, as can be shown from the efficiency formula in equation 4, consumes approximately two-thirds the supply power for a given output-power level than operation from 5-V supplies.



#### APPLICATION INFORMATION

#### headroom and thermal considerations

Linear power amplifiers dissipate a significant amount of heat in the package under normal operating conditions. A typical music CD requires 12 dB to 15 dB of dynamic headroom to pass the loudest portions without distortion as compared with the average power output. From the TPA321 data sheet, one can see that when the TPA321 is operating from a 5-V supply into a  $8-\Omega$  speaker 350 mW peaks are available. Converting watts to dB:

$$P_{dB} = 10 Log \frac{P_W}{P_{ref}} = 10 Log \frac{350 \text{ mW}}{1 \text{ W}} = -4.6 \text{ dB}$$

Subtracting the headroom restriction to obtain the average listening level without distortion yields:

$$-4.6 \text{ dB} - 15 \text{ dB} = -19.6 \text{ dB}$$
 (15 dB headroom)

$$-4.6 \text{ dB} - 12 \text{ dB} = -16.6 \text{ dB}$$
 (12 dB headroom)

$$-4.6 \text{ dB} - 9 \text{ dB} = -13.6 \text{ dB}$$
 (9 dB headroom)

$$-4.6 \text{ dB} - 6 \text{ dB} = -10.6 \text{ dB}$$
 (6 dB headroom)

$$-4.6 \text{ dB} - 3 \text{ dB} = -7.6 \text{ dB}$$
 (3 dB headroom)

Converting dB back into watts:

$$P_W = 10^{PdB/10} x P_{ref}$$

= 11 mW (15 dB headroom)

= 22 mW (12 dB headroom)

= 44 mW (9 dB headroom)

= 88 mW (6 dB headroom)

= 175 mW (3 dB headroom)

This is valuable information to consider when attempting to estimate the heat dissipation requirements for the amplifier system. Comparing the absolute worst case, which is 350 mW of continuous power output with 0 dB of headroom, against 12 dB and 15 dB applications drastically affects maximum ambient temperature ratings for the system. Using the power dissipation curves for a 5-V,  $8-\Omega$  system, the internal dissipation in the TPA321 and maximum ambient temperatures is shown in Table 2.

Table 2. TPA321 Power Rating, 5-V, 8-Ω, BTL

| PEAK OUTPUT POWER (mW) | AVERAGE OUTPUT POWER | POWER DISSIPATION<br>(mW) | MAXIMUM AMBIENT<br>TEMPERATURE |
|------------------------|----------------------|---------------------------|--------------------------------|
| (11144)                |                      | (11144)                   | 0 CFM                          |
| 350                    | 350 mW               | 600                       | 46°C                           |
| 350                    | 175 mW (3 dB)        | 500                       | 64°C                           |
| 350                    | 88 mW (6 dB)         | 380                       | 85°C                           |
| 350                    | 44 mW (9 dB)         | 300                       | 98°C                           |
| 350                    | 22 mW (12 dB)        | 200                       | 115°C                          |
| 350                    | 11 mW (15 dB)        | 180                       | 119°C                          |

Table 2 shows that the TPA321 can be used to its full 350-mW rating without any heat sinking in still air up to 46°C.

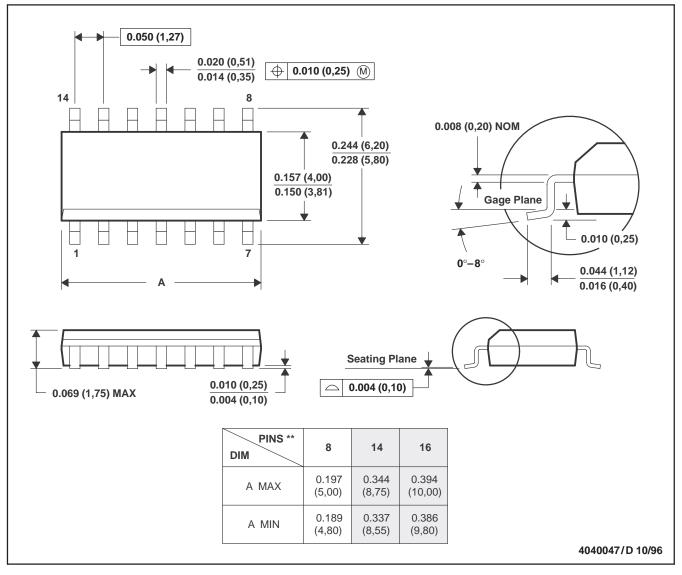


## **MECHANICAL DATA**

## D (R-PDSO-G\*\*)

#### 14 PINS SHOWN

#### PLASTIC SMALL-OUTLINE PACKAGE



NOTES: A. All linear dimensions are in inches (millimeters).

B. This drawing is subject to change without notice.

C. Body dimensions do not include mold flash or protrusion, not to exceed 0.006 (0,15).

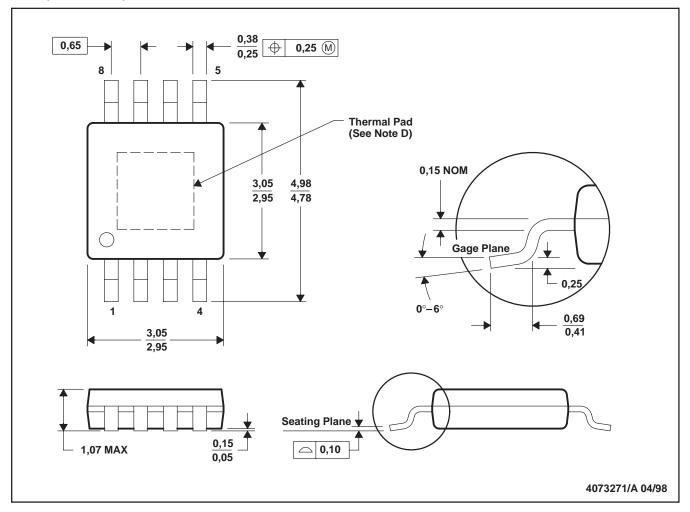
D. Falls within JEDEC MS-012



#### **MECHANICAL DATA**

## DGN (S-PDSO-G8)

## PowerPAD™ PLASTIC SMALL-OUTLINE PACKAGE



NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Body dimensions include mold flash or protrusions.
- D. The package thermal performance may be enhanced by attaching an external heat sink to the thermal pad. This pad is electrically and thermally connected to the backside of the die and possibly selected leads.
- E. Falls within JEDEC MO-187

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